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November 2013

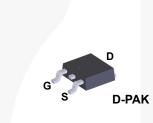
FQD10N20L **N-Channel QFET® MOSFET** 200 V, 7.6 A, 360 mΩ

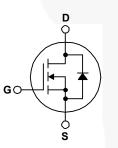
Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance • Low Crss (Typ. 14 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power • 100% Avalanche Tested factor correction (PFC), and electronic lamp ballasts.

Features

- 7.6 A, 200 V, R_{DS(on)} = 360 mΩ (Max.) @ V_{GS} = 10 V, $I_{D} = 3.8 \text{ A}$
- Low Gate Charge (Typ. 13 nC)
- · Low Level Gate Drive Requirements Allowing **Direct Operation Form Logic Drivers**





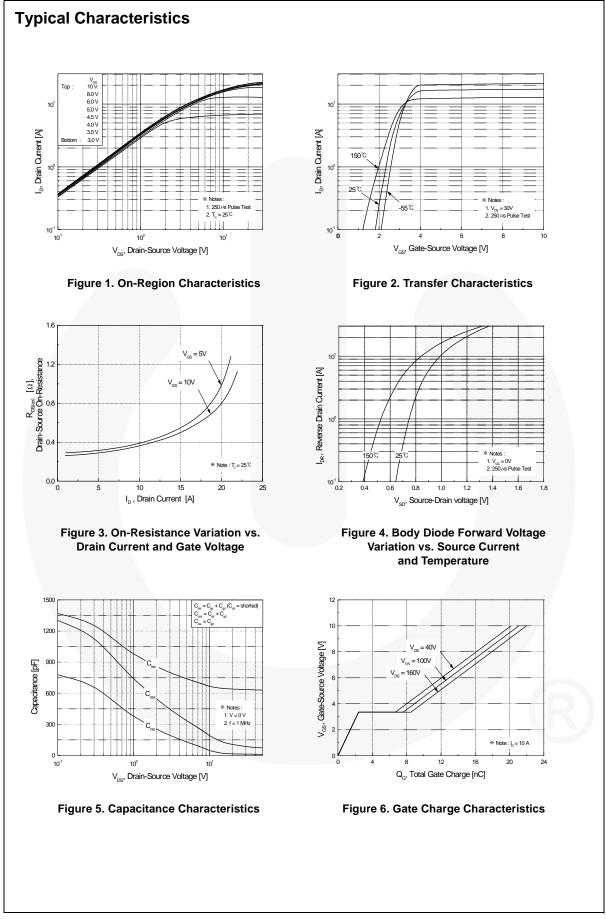
Absolute Maximum Ratings T_c = 25°C unless otherwise noted.

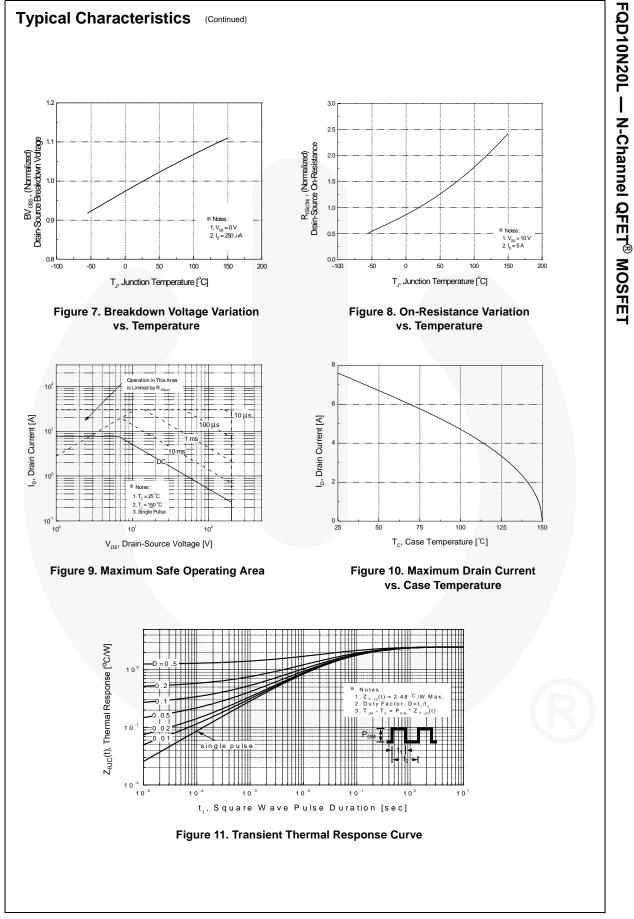
Symbol	Parameter		FQD10N20LTM	Unit
V _{DSS}	Drain-Source Voltage		200	V
I _D	Drain Current - Continuous ($T_C = 25^{\circ}C$)		7.6	A
	- Continuous (T _C = 100°C)		4.8	A
I _{DM}	Drain Current - Pulsed	(Note 1)	30.4	A
V _{GSS}	Gate-Source Voltage		± 20	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	180	mJ
I _{AR}	Avalanche Current	(Note 1)	7.6	A
E _{AR}	Repetitive Avalanche Energy	(Note 1)	5.1	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	5.5	V/ns
PD	Power Dissipation ($T_A = 25^{\circ}C$) *		2.5	W
	Power Dissipation ($T_C = 25^{\circ}C$)		51	W
	- Derate above 25°C		0.4	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C
ΤL	Maximum lead temperature for soldering, 1/8" from case for 5 seconds		300	°C

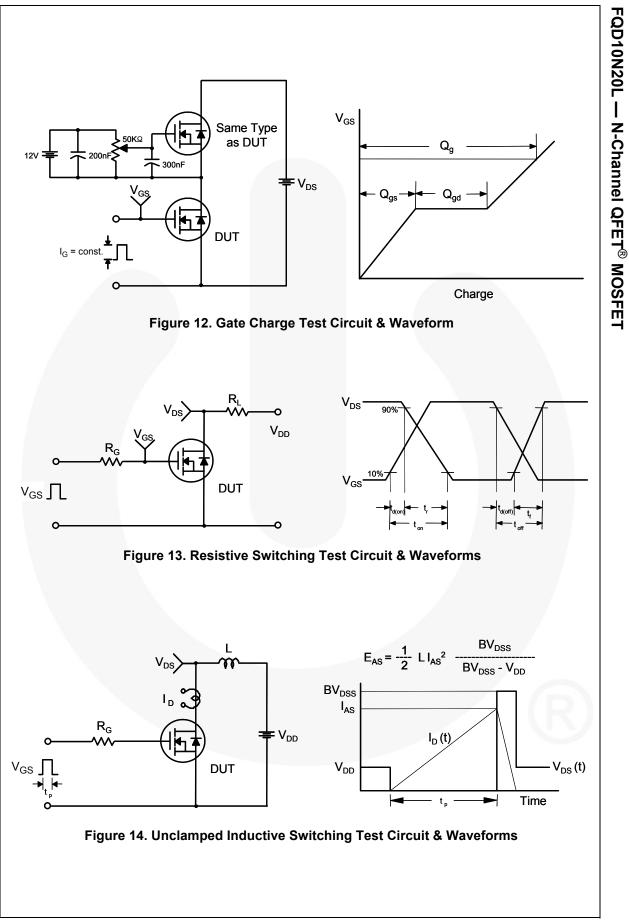
Thermal Characteristics

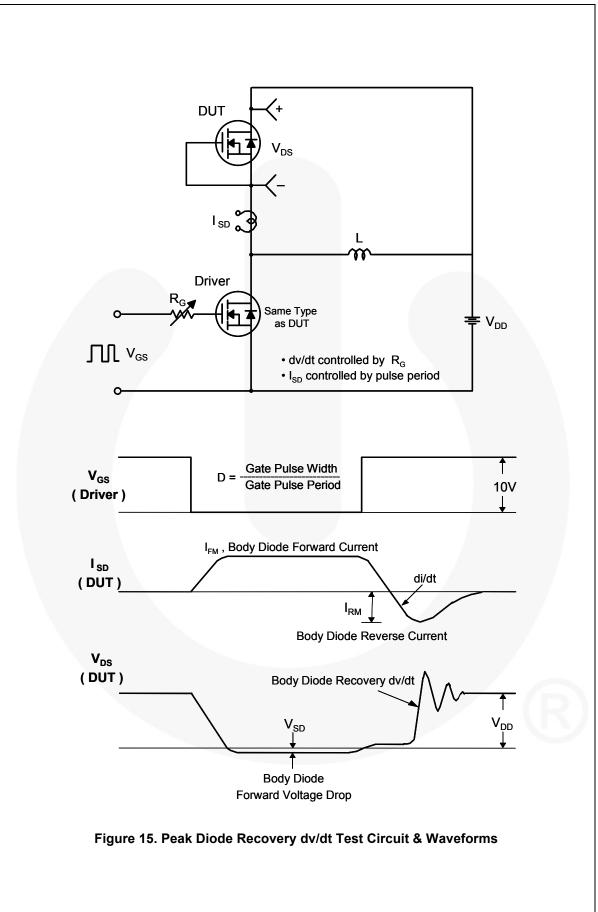
Symbol	Parameter	FQD10N20LTM	Unit
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	2.48	
D	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	110	°C/W
R_{\thetaJA}	Thermal Resistance, Junction to Ambient (*1 in ² Pad of 2-oz Copper), Max.	50	

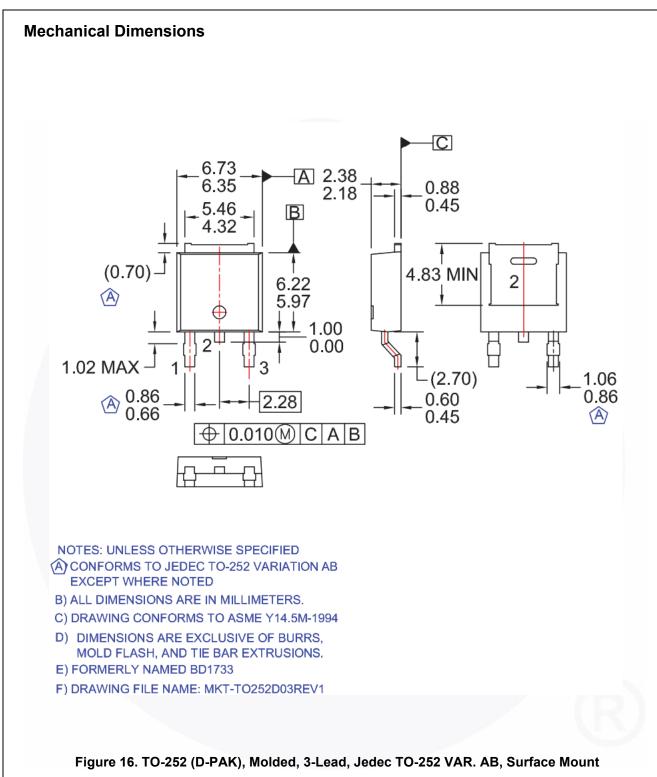
Symbol Off Cha ^{BV_{DSS}}	_	•		· j· · · · · · · · · · · · · · · · · ·		Reel 330		Tape Width 16 mm		Quantity 2500 units	
Off Cha BV _{DSS}	cal Char	acteristics	T _C = 25°	C unless oth	nerwise noted.						
BV _{DSS}		Parameter			Test Con	ditions		Min.	Тур.	Max	. Unit
BV _{DSS}	aractoristic	re i									
		ce Breakdown Vo	Itage	$V_{CS} = 0$	0 V, I _D = 25	50 uA		200			V
∆BV _{DSS}	Breakdown Voltage Temperature		0					200			
$/\Delta T_J$	Coefficient		$I_D = 250 \ \mu A$, Referenced to 25°C					0.18		V/°C	
I _{DSS}				$V_{DS} = 200 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 160 \text{ V}, T_C = 125^{\circ}\text{C}$						1	μΑ
	Zero Gate Voltage Drain Current								10	μΑ	
I _{GSSF}	Gate-Body	Leakage Current	, Forward	$V_{GS} = 20 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$						100	nA
I _{GSSR}	Gate-Body	Leakage Current	Reverse	$V_{GS} = -$	-20 V, V _{DS}	= 0 V		-		-100	nA
On Cha	aracteristic										
V _{GS(th)}		hold Voltage	_		√ _{GS} , I _D = 2	50 µA		1.0		2.0	V
R _{DS(on)}	Static Drain	0		_	10 V, I _D = 3		-	1.0	0.29	0.36	-
DS(on)	On-Resistar			00	5 V, I _D = 3.				0.29	0.30	Ω
9 _{FS}	Forward Tra	ansconductance	_		30 V, I _D = 3				9.6		S
				1					I		
	ic Charact		_	i					1	1	
C _{iss}	Input Capad		_	$V_{DS} = 2$	25 V, V _{GS} =	= 0 V,			640	830	pF
C _{oss}	Output Cap		_	f = 1.0	MHz				95	125	pF
C _{rss}	Reverse Ira	ansfer Capacitan	ce						14	18	pF
Switchi	ing Charac	cteristics									
Switchi t _{d(on)}	Turn-On De			<u> </u>	100 \/ _	10.4			13	35	ns
t _{d(on)}		elay Time			100 V, I _D =	10 A,			13 150	35 310	ns
	Turn-On De	elay Time se Time	_	V _{DD} = 7 R _G = 2	5		(Note 4)		-		-
t _{d(on)} t _r t _{d(off)}	Turn-On De Turn-On Ris	elay Time se Time elay Time			5		(Note 4)		150	310	ns
t _{d(on)} t _r	Turn-On De Turn-On Ris Turn-Off De	elay Time se Time elay Time III Time		$R_{G} = 2$	5Ω		(Note 4)		150 50	310 110	ns
t _{d(on)} t _r t _{d(off)} t _f	Turn-On De Turn-On Ris Turn-Off De Turn-Off Fa	elay Time se Time elay Time III Time Charge		$R_{G} = 2$	5 Ω 160 V, I _D =	10 A,	(Note 4)		150 50 95	310 110 200	ns ns ns
^t d(on) tr td(off) tf Qg Qgs	Turn-On De Turn-On Ris Turn-Off De Turn-Off Fa Total Gate (elay Time se Time elay Time II Time Charge re Charge		$R_G = 2$	5 Ω 160 V, I _D =	10 A,			150 50 95 13	310 110 200 17	ns ns ns nC
t _{d(on)} t _r t _{d(off)} t _f Q _g Q _{gs} Q _{gd}	Turn-On De Turn-On Ris Turn-Off De Turn-Off Fa Total Gate C Gate-Sourc Gate-Drain	elay Time se Time elay Time Il Time Charge Charge Charge		V _{DS} = 2 V _{DS} = 7 V _{GS} = 5	5 Ω 160 V, I _D = 5 V	10 A,		 	150 50 95 13 2.4	310 110 200 17 	ns ns ns nC nC
t _{d(on)} t _r t _{d(off)} t _f Q _g Q _{gs} Q _{gd} Drain-S	Turn-On De Turn-On Ris Turn-Off De Turn-Off Fa Total Gate C Gate-Sourc Gate-Drain	elay Time se Time elay Time II Time Charge Charge Charge		$R_G = 2$ $V_{DS} = 7$ $V_{GS} = 5$	5 Ω 160 V, I _D = 5 V imum R	10 A, atings		 	150 50 95 13 2.4	310 110 200 17 	ns ns ns nC nC
t _{d(on)} t _r t _{d(off)} t _f Q _{gs} Q _{gd} Drain-S	Turn-On De Turn-On Ris Turn-Off De Turn-Off Fa Total Gate C Gate-Sourc Gate-Drain Source Dio Maximum C	elay Time se Time elay Time III Time Charge charge Charge de Characte Continuous Drain-	Source Dic	$R_{G} = 2$ $V_{DS} = 2$ $V_{GS} = 3$ $V_{GS} = 3$ $M = 1$ $M = 1$	5 Ω $160 V, I_D =$ 5 V imum R ard Curren	10 A, atings		 	150 50 95 13 2.4	310 110 200 17 7.6	ns ns nC nC nC A
^t d(on) t _r t _{d(off)} t _f Q _{gs} Q _{gd} Drain-S I _S	Turn-On De Turn-On Ris Turn-Off De Turn-Off Fa Total Gate C Gate-Sourc Gate-Drain Source Dio Maximum C Maximum P	elay Time se Time elay Time III Time Charge charge Charge ode Character Continuous Drain- Pulsed Drain-Sour	Source Dic rce Diode F	$R_G = 2$ $V_{DS} = 7$ $V_{GS} = 8$ M Max ode Forward C	5Ω $160 V, I_D =$ 5 V imum R ard Current Current	10 A, atings t			150 50 95 13 2.4 6.1	310 110 200 17 7.6 30.4	ns ns nc nC nC A
^t d(on) t _r ^t d(off) t _f Q _g Q _{gd} Drain-S I _S I _{SM} V _{SD}	Turn-On De Turn-On Ris Turn-Off De Turn-Off Fa Total Gate (Gate-Sourc Gate-Drain Source Dio Maximum C Maximum P Drain-Source	elay Time se Time elay Time II Time Charge Charge Charge de Character Continuous Drain- Pulsed Drain-Source ce Diode Forward	Source Dic rce Diode F	$R_{G} = 2$ $V_{DS} = 2$ $V_{GS} = 3$ $V_{GS} = 3$ $M = 1$ $M = 1$ $M = 2$ $M = 1$ $M = 2$ M	5 Ω 160 V, $I_D = 5$ 5 V imum R ard Current Current D V, $I_S = 7$.	10 A, atings t 6 A			150 50 95 13 2.4 6.1	310 110 200 17 7.6	ns ns nC nC nC A
^t d(on) t _r t _{d(off)} t _f Q _{gs} Q _{gd} Drain-S I _S	Turn-On De Turn-On Ris Turn-Off De Turn-Off Fa Total Gate (Gate-Sourc Gate-Drain Source Dio Maximum C Maximum P Drain-Sourc Reverse Re	elay Time se Time elay Time III Time Charge charge Charge ode Character Continuous Drain- Pulsed Drain-Sour	Source Dic rce Diode F	$R_{G} = 2$ $V_{DS} = 2$ $V_{GS} = 4$	5Ω $160 V, I_D =$ 5 V imum R ard Current Current	10 A, atings t 6 A 0 A,			150 50 95 13 2.4 6.1	310 110 200 17 7.6 30.4	ns ns ns nC nC nC A











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